



Welcome to [E-XFL.COM](https://www.e-xfl.com)

What is "[Embedded - Microcontrollers](#)"?

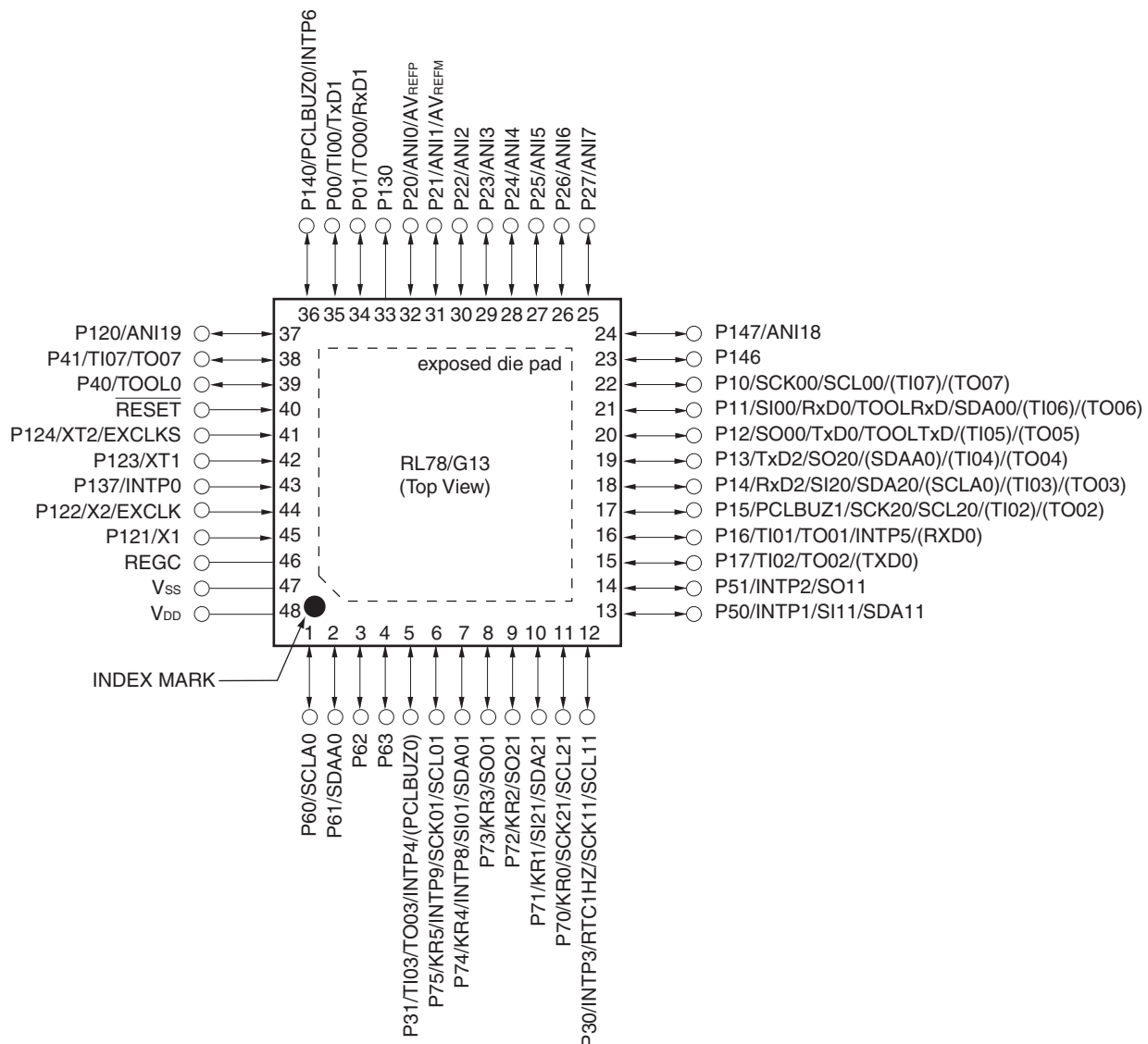
"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 20x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x20)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100pfafa-v0

- 48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)

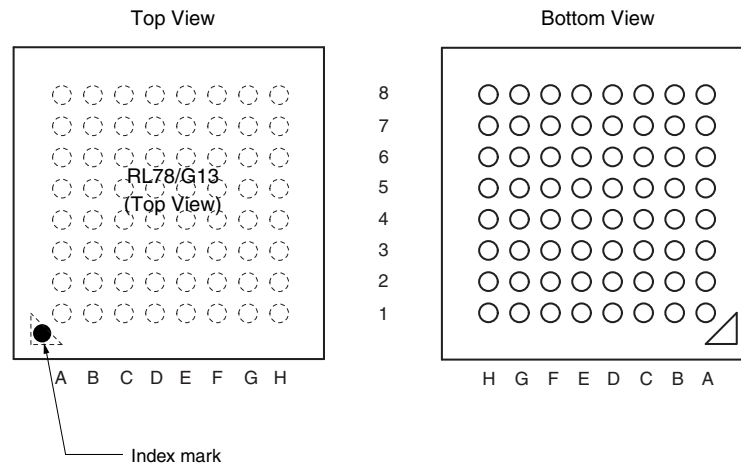


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.
- It is recommended to connect an exposed die pad to Vss.

- 64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)



Pin No.	Name	Pin No.	Name	Pin No.	Name	Pin No.	Name
A1	P05/TI05/TO05	C1	P51/INTP2/SO11	E1	P13/TxD2/SO20/(SDAA0)/(TI04)/(TO04)	G1	P146
A2	P30/INTP3/RTC1HZ/SCK11/SCL11	C2	P71/KR1/SI21/SDA21	E2	P14/RxD2/SI20/SDA20/(SCLA0)/(TI03)/(TO03)	G2	P25/ANI5
A3	P70/KR0/SCK21/SCL21	C3	P74/KR4/INTP8/SI01/SDA01	E3	P15/SCK20/SCL20/(TI02)/(TO02)	G3	P24/ANI4
A4	P75/KR5/INTP9/SCK01/SCL01	C4	P52/(INTP10)	E4	P16/TI01/TO01/INTP5/(SI00)/(RxD0)	G4	P22/ANI2
A5	P77/KR7/INTP11/(TxD2)	C5	P53/(INTP11)	E5	P03/ANI16/SI10/RxD1/SDA10	G5	P130
A6	P61/SDAA0	C6	P63	E6	P41/TI07/TO07	G6	P02/ANI17/SO10/TxD1
A7	P60/SCLA0	C7	V _{SS}	E7	RESET	G7	P00/TI00
A8	EV _{DD0}	C8	P121/X1	E8	P137/INTP0	G8	P124/XT2/EXCLKS
B1	P50/INTP1/SI11/SDA11	D1	P55/(PCLBUZ1)/(SCK00)	F1	P10/SCK00/SCL00/(TI07)/(TO07)	H1	P147/ANI18
B2	P72/KR2/SO21	D2	P06/TI06/TO06	F2	P11/SI00/RxD0/TOOLRxD/SDA00/(TI06)/(TO06)	H2	P27/ANI7
B3	P73/KR3/SO01	D3	P17/TI02/TO02/(SO00)/(TxD0)	F3	P12/SO00/TxD0/TOOLTxD/(INTP5)/(TI05)/(TO05)	H3	P26/ANI6
B4	P76/KR6/INTP10/(RxD2)	D4	P54	F4	P21/ANI1/AV _{REFM}	H4	P23/ANI3
B5	P31/TI03/TO03/INTP4/(PCLBUZ0)	D5	P42/TI04/TO04	F5	P04/SCK10/SCL10	H5	P20/ANI0/AV _{REFP}
B6	P62	D6	P40/TOOL0	F6	P43	H6	P141/PCLBUZ1/INTP7
B7	V _{DD}	D7	REGC	F7	P01/TO00	H7	P140/PCLBUZ0/INTP6
B8	EV _{SS0}	D8	P122/X2/EXCLK	F8	P123/XT1	H8	P120/ANI19

Cautions 1. Make EV_{SS0} pin the same potential as V_{SS} pin.

2. Make V_{DD} pin the potential that is higher than EV_{DD0} pin.

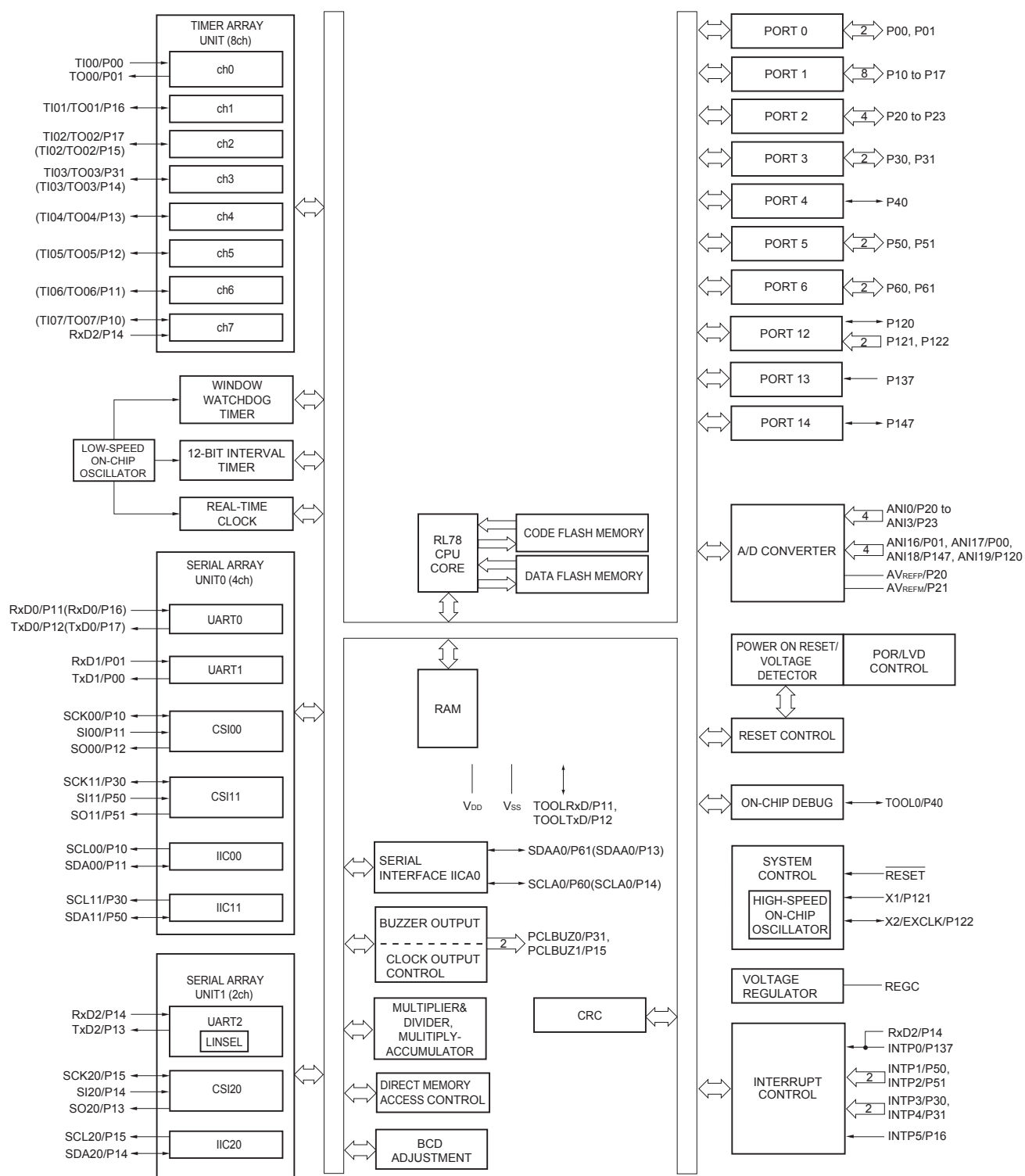
3. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the V_{SS} and EV_{SS0} pins to separate ground lines.

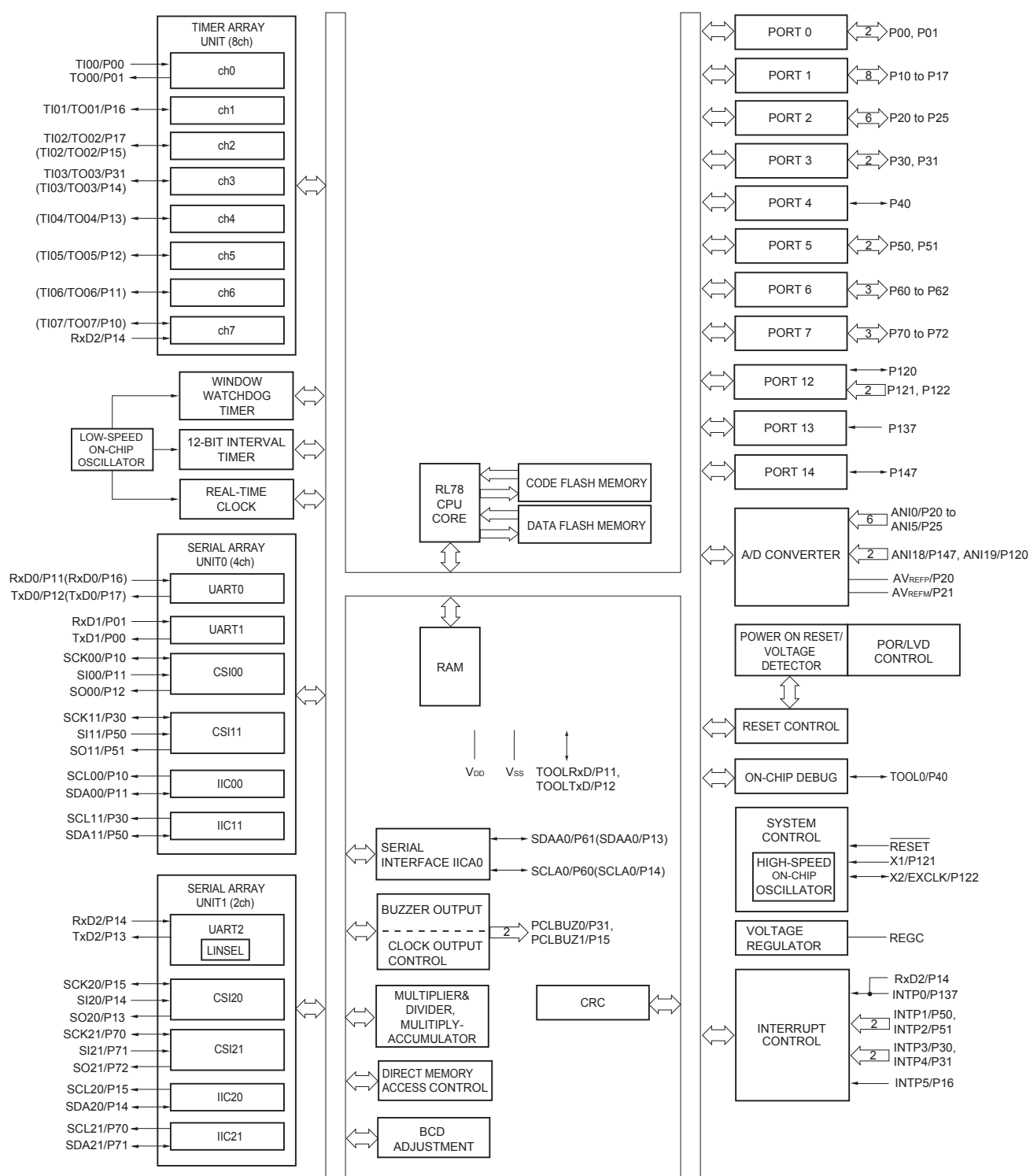
3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.4 30-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.6 36-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.6 Outline of Functions

[20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item		20-pin		24-pin		25-pin		30-pin		32-pin		36-pin	
		R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F100Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Code flash memory (KB)		16 to 64		16 to 64		16 to 64		16 to 128		16 to 128		16 to 128	
Data flash memory (KB)		4	–	4	–	4	–	4 to 8	–	4 to 8	–	4 to 8	–
RAM (KB)		2 to 4 ^{Note1}		2 to 4 ^{Note1}		2 to 4 ^{Note1}		2 to 12 ^{Note1}		2 to 12 ^{Note1}		2 to 12 ^{Note1}	
Address space		1 MB											
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)											
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)											
Subsystem clock		–											
Low-speed on-chip oscillator		15 kHz (TYP.)											
General-purpose registers		(8-bit register × 8) × 4 banks											
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator: f _{IH} = 32 MHz operation)											
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)											
Instruction set		<ul style="list-style-type: none">• Data transfer (8/16 bits)• Adder and subtractor/logical operation (8/16 bits)• Multiplication (8 bits × 8 bits)• Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.											
I/O port	Total	16	20	21	26	28	32						
	CMOS I/O	13 (N-ch O.D. I/O [V _{DD} withstand voltage]: 5)	15 (N-ch O.D. I/O [V _{DD} withstand voltage]: 6)	15 (N-ch O.D. I/O [V _{DD} withstand voltage]: 6)	21 (N-ch O.D. I/O [V _{DD} withstand voltage]: 9)	22 (N-ch O.D. I/O [V _{DD} withstand voltage]: 9)	26 (N-ch O.D. I/O [V _{DD} withstand voltage]: 10)						
	CMOS input	3	3	3	3	3	3						
	CMOS output	–	–	1	–	–	–						
	N-ch O.D. I/O (withstand voltage: 6 V)	–	2	2	2	3	3						
Timer	16-bit timer	8 channels											
	Watchdog timer	1 channel											
	Real-time clock (RTC)	1 channel ^{Note 2}											
	12-bit interval timer (IT)	1 channel											
	Timer output	3 channels (PWM outputs: 2 ^{Note 3})	4 channels (PWM outputs: 3 ^{Note 3})				4 channels (PWM outputs: 3 ^{Note 3}), 8 channels (PWM outputs: 7 ^{Note 3}) ^{Note 4}						
	RTC output	–											

- Notes**
- The flash library uses RAM in self-programming and rewriting of the data flash memory. The target products and start address of the RAM areas used by the flash library are shown below.
 R5F100xD, R5F101xD (x = 6 to 8, A to C): Start address FF300H
 R5F100xE, R5F101xE (x = 6 to 8, A to C): Start address FEF00H
 For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.
 - Only the constant-period interrupt function when the low-speed on-chip oscillator clock (f_{IL}) is selected

[40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item		40-pin		44-pin		48-pin		52-pin		64-pin	
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx
Code flash memory (KB)		16 to 192		16 to 512		16 to 512		32 to 512		32 to 512	
Data flash memory (KB)		4 to 8	—	4 to 8	—	4 to 8	—	4 to 8	—	4 to 8	—
RAM (KB)		2 to 16 ^{Note1}		2 to 32 ^{Note1}		2 to 32 ^{Note1}		2 to 32 ^{Note1}		2 to 32 ^{Note1}	
Address space		1 MB									
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)									
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)									
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz									
Low-speed on-chip oscillator		15 kHz (TYP.)									
General-purpose registers		(8-bit register × 8) × 4 banks									
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator: f _{IH} = 32 MHz operation)									
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)									
		30.5 μs (Subsystem clock: f _{SUB} = 32.768 kHz operation)									
Instruction set		<ul style="list-style-type: none">• Data transfer (8/16 bits)• Adder and subtractor/logical operation (8/16 bits)• Multiplication (8 bits × 8 bits)• Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.									
I/O port	Total	36		40		44		48		58	
	CMOS I/O	28 (N-ch O.D. I/O [V _{DD} withstand voltage]: 10)		31 (N-ch O.D. I/O [V _{DD} withstand voltage]: 10)		34 (N-ch O.D. I/O [V _{DD} withstand voltage]: 11)		38 (N-ch O.D. I/O [V _{DD} withstand voltage]: 13)		48 (N-ch O.D. I/O [V _{DD} withstand voltage]: 15)	
	CMOS input	5		5		5		5		5	
	CMOS output	—		—		1		1		1	
	N-ch O.D. I/O (withstand voltage: 6 V)	3		4		4		4		4	
Timer	16-bit timer	8 channels									
	Watchdog timer	1 channel									
	Real-time clock (RTC)	1 channel									
	12-bit interval timer (IT)	1 channel									
	Timer output	4 channels (PWM outputs: 3 ^{Note2}), 8 channels (PWM outputs: 7 ^{Note2, Note3})		5 channels (PWM outputs: 4 ^{Note2}), 8 channels (PWM outputs: 7 ^{Note2}) ^{Note3}						8 channels (PWM outputs: 7 ^{Note2})	
	RTC output	1 channel • 1 Hz (subsystem clock: f _{SUB} = 32.768 kHz)									

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory. The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = E to G, J, L): Start address FF300H

R5F100xE, R5F101xE (x = E to G, J, L): Start address FEF00H

R5F100xJ, R5F101xJ (x = F, G, J, L): Start address FAF00H

R5F100xL, R5F101xL (x = F, G, J, L): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

(T_A = -40 to +85°C, 1.6 V ≤ E_{VDD0} = E_{VDD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = E_{VSS0} = E_{VSS1} = 0 V) (5/5)

Items	Symbol	Conditions	MIN.		TYP.	MAX.	Unit	
Input leakage current, high	I _{LIH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	V _I = EV _{DD0}			1	μA	
	I _{LIH2}	P20 to P27, P137, P150 to P156, RESET	V _I = V _{DD}			1	μA	
	I _{LIH3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	V _I = V _{DD}	In input port or external clock input		1	μA	
				In resonator connection		10	μA	
Input leakage current, low	I _{LIL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	V _I = EV _{SS0}			−1	μA	
	I _{LIL2}	P20 to P27, P137, P150 to P156, RESET	V _I = V _{SS}			−1	μA	
	I _{LIL3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	V _I = V _{SS}	In input port or external clock input		−1	μA	
				In resonator connection		−10	μA	
On-chip pll-up resistance	R _U	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	V _I = EV _{SS0} , In input port		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only) (1/2)

(T_A = -40 to +85°C, 2.7 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t _{KCY1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 20 pF, R _b = 1.4 kΩ	200		1150		1150		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ	300		1150		1150		ns
SCKp high-level width	t _{KH1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 20 pF, R _b = 1.4 kΩ	t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ	t _{KCY1} /2 – 120		t _{KCY1} /2 – 120		t _{KCY1} /2 – 120		ns
SCKp low-level width	t _{KL1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 20 pF, R _b = 1.4 kΩ	t _{KCY1} /2 – 7		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ	t _{KCY1} /2 – 10		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns
Slp setup time (to SCKp↑) ^{Note 1}	t _{SIK1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 20 pF, R _b = 1.4 kΩ	58		479		479		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ	121		479		479		ns
Slp hold time (from SCKp↑) ^{Note 1}	t _{KSI1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 20 pF, R _b = 1.4 kΩ	10		10		10		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ	10		10		10		ns
Delay time from SCKp↓ to SOp output ^{Note 1}	t _{KSO1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 20 pF, R _b = 1.4 kΩ		60		60		60	ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ		130		130		130	ns

(Notes, Caution, and Remarks are listed on the next page.)

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (1/2)(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f _{SCL}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 50 pF, R _b = 2.7 kΩ		1000 Note 1		300 Note 1		300 Note 1	kHz
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ		1000 Note 1		300 Note 1		300 Note 1	kHz
		4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ		400 Note 1		300 Note 1		300 Note 1	kHz
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ		400 Note 1		300 Note 1		300 ote 1	kHz
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 100 pF, R _b = 5.5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
Hold time when SCLr = "L"	t _{LOW}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 50 pF, R _b = 2.7 kΩ	475		1550		1550		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ	475		1550		1550		ns
		4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	1150		1550		1550		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	1150		1550		1550		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 100 pF, R _b = 5.5 kΩ	1550		1550		1550		ns
Hold time when SCLr = "H"	t _{HIGH}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 50 pF, R _b = 2.7 kΩ	245		610		610		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ	200		610		610		ns
		4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	675		610		610		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	600		610		610		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 100 pF, R _b = 5.5 kΩ	610		610		610		ns

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (-) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V		1.2	±7.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V <small>Note 3</small>		1.2	±10.5	LSB
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ V _{DD} ≤ 5.5 V	57		95	μs
Conversion time	t _{CONV}	10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V _{DD} ≤ 5.5 V <small>Note 3</small>			±0.85	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V _{DD} ≤ 5.5 V <small>Note 3</small>			±0.85	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±4.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V <small>Note 3</small>			±6.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±2.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V <small>Note 3</small>			±2.5	LSB
Analog input voltage	V _{AIN}	ANI0 to ANI14	0			V _{DD}	V
		ANI16 to ANI26	0			EV _{DD0}	V
		Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)	V _{BGR} ^{Note 4}				V
		Temperature sensor output voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)	V _{TMPS25} ^{Note 4}				V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

4. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

LVD Detection Voltage of Interrupt & Reset Mode(T_A = -40 to +85°C, V_{PDR} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	VLVDA0	V _{POC2} , V _{POC1} , V _{POC0} = 0, 0, 0, falling reset voltage		1.60	1.63	1.66	V
	VLVDA1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
			Falling interrupt voltage	1.70	1.73	1.77	V
	VLVDA2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
			Falling interrupt voltage	1.80	1.84	1.87	V
	VLVDA3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDB0	V _{POC2} , V _{POC1} , V _{POC0} = 0, 0, 1, falling reset voltage		1.80	1.84	1.87	V
	VLVDB1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
			Falling interrupt voltage	1.90	1.94	1.98	V
	VLVDB2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
			Falling interrupt voltage	2.00	2.04	2.08	V
	VLVDB3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
			Falling interrupt voltage	3.00	3.06	3.12	V
	VLVDC0	V _{POC2} , V _{POC1} , V _{POC0} = 0, 1, 0, falling reset voltage		2.40	2.45	2.50	V
	VLVDC1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
			Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
			Falling interrupt voltage	2.60	2.65	2.70	V
	VLVDC3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
			Falling interrupt voltage	3.60	3.67	3.74	V
	VLVDD0	V _{POC2} , V _{POC1} , V _{POC0} = 0, 1, 1, falling reset voltage		2.70	2.75	2.81	V
	VLVDD1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDD2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
			Falling interrupt voltage	2.90	2.96	3.02	V
	VLVDD3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
			Falling interrupt voltage	3.90	3.98	4.06	V

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current Note 1	I _{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.62	3.40	mA	
					V _{DD} = 3.0 V		0.62	3.40	mA	
				f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	2.70	mA	
					V _{DD} = 3.0 V		0.50	2.70	mA	
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.44	1.90	mA	
					V _{DD} = 3.0 V		0.44	1.90	mA	
			HS (high-speed main) mode Note 7	f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.31	2.10	mA	
					Resonator connection		0.48	2.20	mA	
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.31	2.10	mA	
					Resonator connection		0.48	2.20	mA	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.21	1.10	mA	
					Resonator connection		0.28	1.20	mA	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.21	1.10	mA	
					Resonator connection		0.28	1.20	mA	
		Subsystem clock operation	f _{SUB} = 32.768 kHz ^{Note 5} T _A = −40°C	Square wave input		0.28	0.61	μA		
				Resonator connection		0.47	0.80	μA		
			f _{SUB} = 32.768 kHz ^{Note 5} T _A = +25°C	Square wave input		0.34	0.61	μA		
				Resonator connection		0.53	0.80	μA		
			f _{SUB} = 32.768 kHz ^{Note 5} T _A = +50°C	Square wave input		0.41	2.30	μA		
				Resonator connection		0.60	2.49	μA		
			f _{SUB} = 32.768 kHz ^{Note 5} T _A = +70°C	Square wave input		0.64	4.03	μA		
				Resonator connection		0.83	4.22	μA		
			f _{SUB} = 32.768 kHz ^{Note 5} T _A = +85°C	Square wave input		1.09	8.04	μA		
				Resonator connection		1.28	8.23	μA		
		f _{SUB} = 32.768 kHz ^{Note 5} T _A = +105°C	Square wave input		5.50	41.00	μA			
			Resonator connection		5.50	41.00	μA			
	I _{DD3} ^{Note 6}	STOP mode Note 8	T _A = −40°C					0.19	0.52	μA
			T _A = +25°C					0.25	0.52	μA
			T _A = +50°C					0.32	2.21	μA
			T _A = +70°C					0.55	3.94	μA
			T _A = +85°C					1.00	7.95	μA
			T _A = +105°C					5.00	40.00	μA

(Notes and Remarks are listed on the next page.)

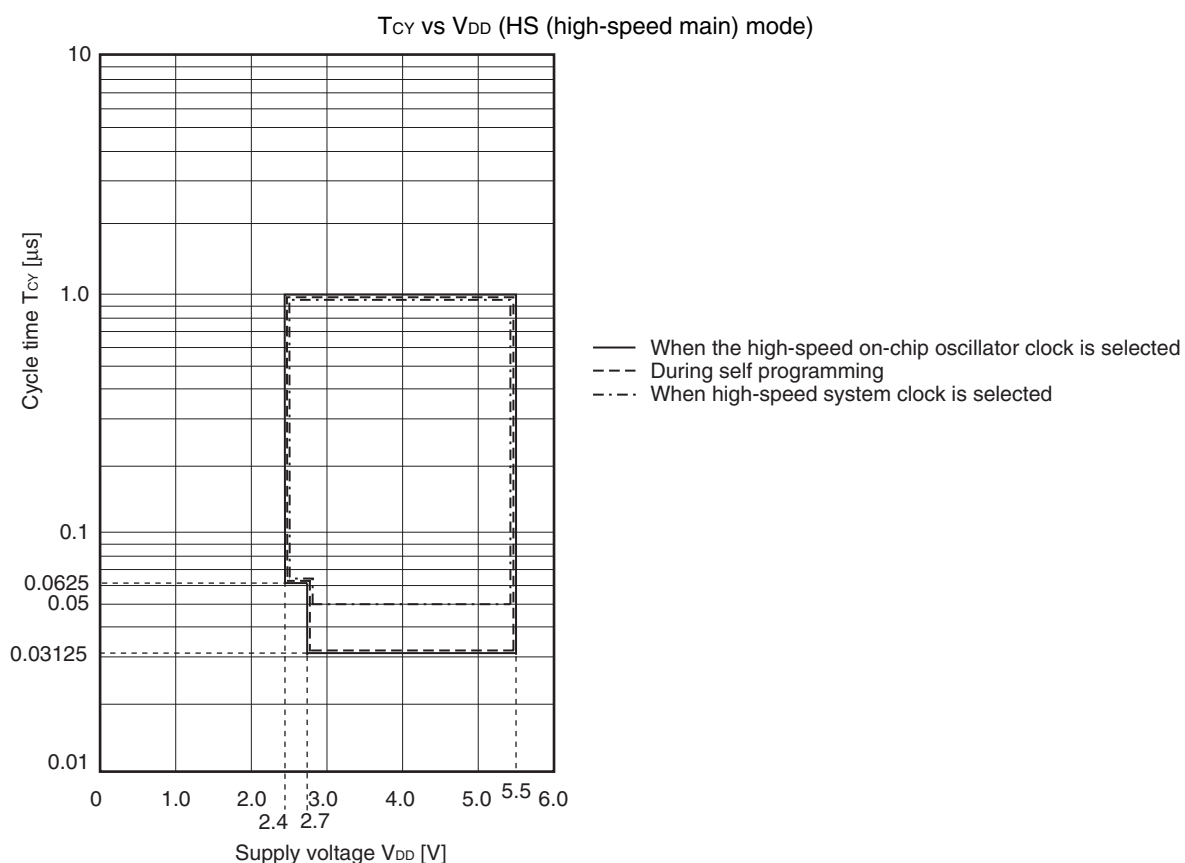
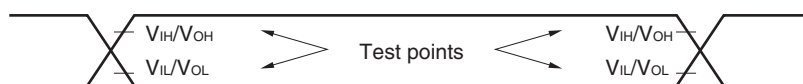
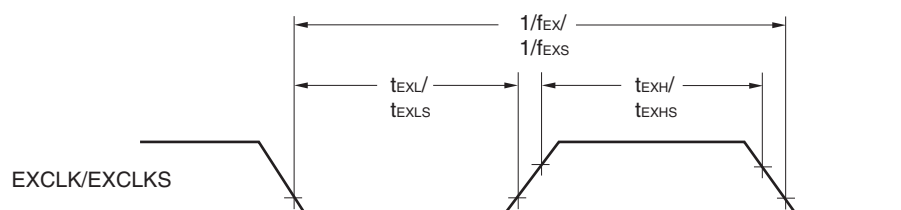
(3) Peripheral Functions (Common to all products)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$)**

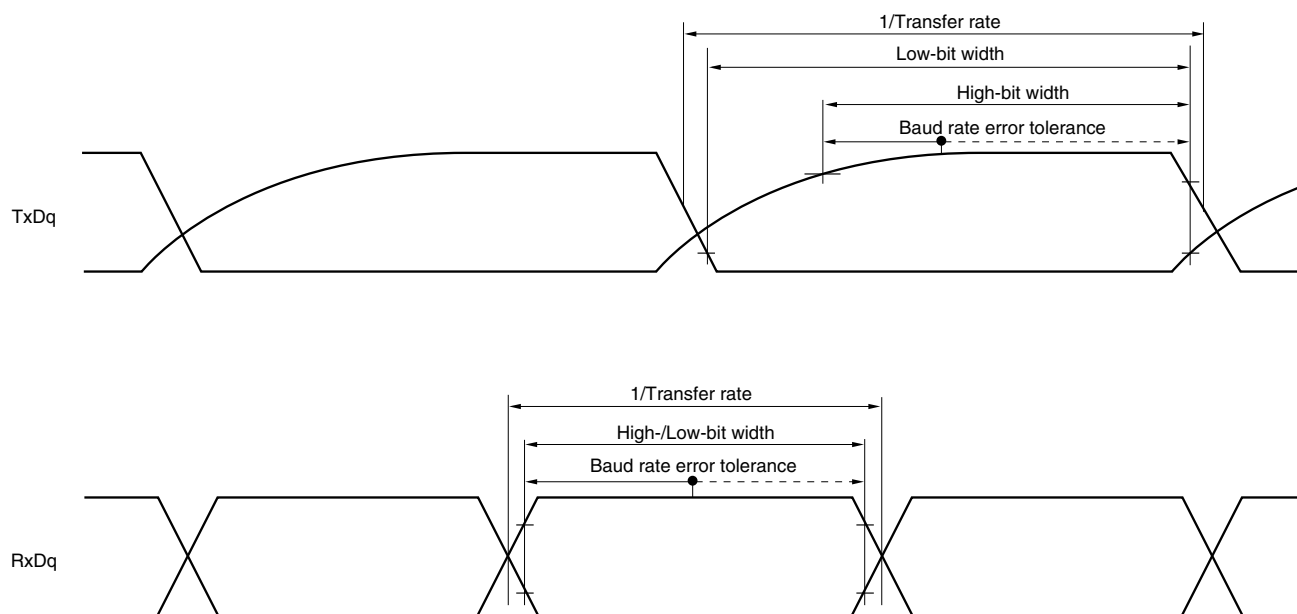
Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I_{FIL} Note 1				0.20		μA
RTC operating current	I_{RTC} Notes 1, 2, 3				0.02		μA
12-bit interval timer operating current	I_{IT} Notes 1, 2, 4				0.02		μA
Watchdog timer operating current	I_{WDT} Notes 1, 2, 5	$f_{\text{IL}} = 15\text{ kHz}$			0.22		μA
A/D converter operating current	I_{ADC} Notes 1, 6	When conversion at maximum speed	Normal mode, $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} = 5.0\text{ V}$		1.3	1.7	mA
			Low voltage mode, $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} = 3.0\text{ V}$		0.5	0.7	mA
A/D converter reference voltage current	I_{ADREF} Note 1				75.0		μA
Temperature sensor operating current	I_{TMPS} Note 1				75.0		μA
LVD operating current	I_{LVD} Notes 1, 7				0.08		μA
Self programming operating current	I_{FSP} Notes 1, 9				2.50	12.20	mA
BGO operating current	I_{BGO} Notes 1, 8				2.50	12.20	mA
SNOOZE operating current	I_{SNOZ} Note 1	ADC operation	The mode is performed ^{Note 10}		0.50	1.10	mA
			The A/D conversion operations are performed, Low voltage mode, $\text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} = 3.0\text{ V}$		1.20	2.04	mA
		CSI/UART operation			0.70	1.54	mA

Notes 1. Current flowing to the V_{DD} .

2. When high speed on-chip oscillator and high-speed system clock are stopped.

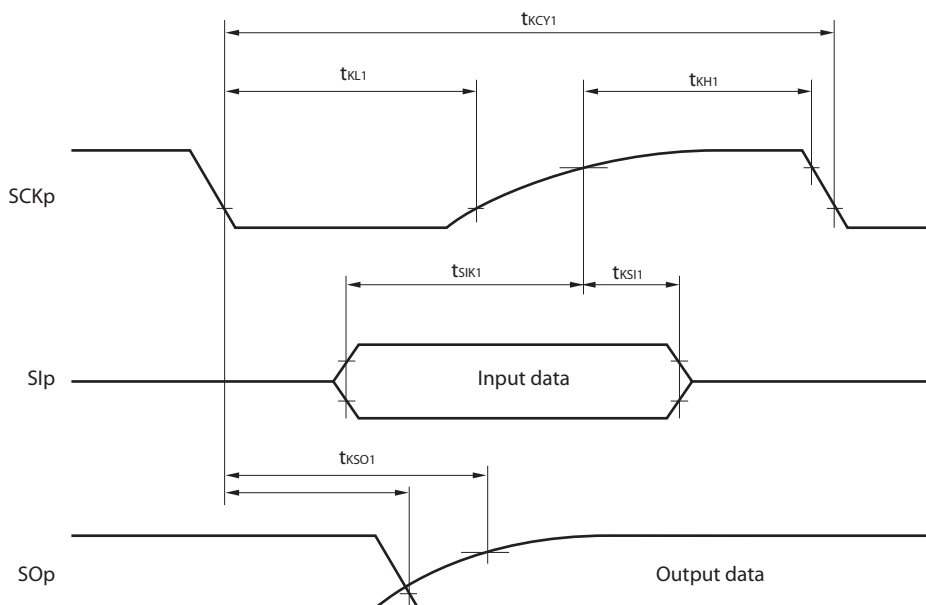
3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either $I_{\text{DD}1}$ or $I_{\text{DD}2}$, and I_{RTC} , when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. $I_{\text{DD}2}$ subsystem clock operation includes the operational current of the real-time clock.4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either $I_{\text{DD}1}$ or $I_{\text{DD}2}$, and I_{IT} , when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 is the sum of $I_{\text{DD}1}$, $I_{\text{DD}2}$ or $I_{\text{DD}3}$ and I_{WDT} when the watchdog timer operates.

Minimum Instruction Execution Time during Main System Clock Operation**AC Timing Test Points****External System Clock Timing**

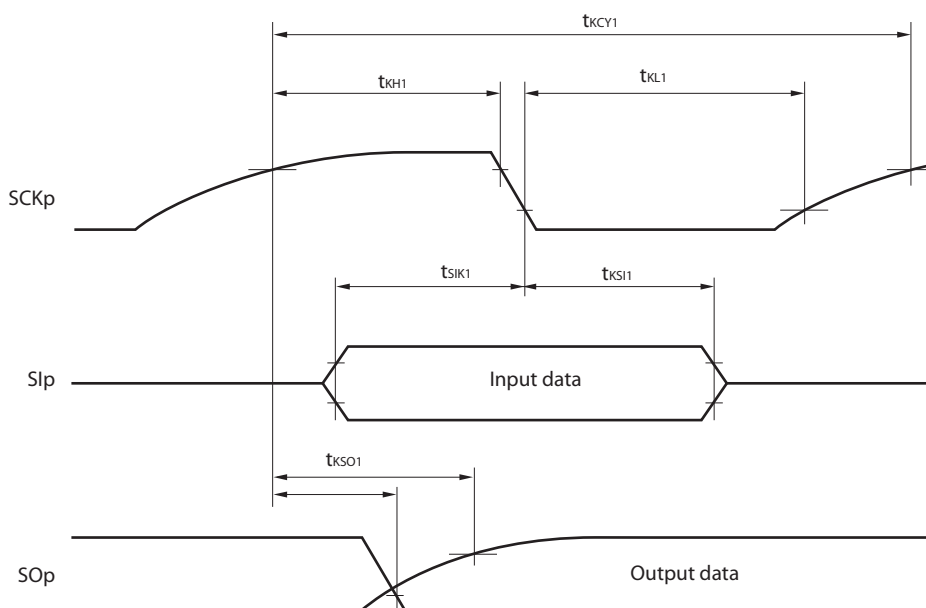
UART mode bit width (during communication at different potential) (reference)

- Remarks**
1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance,
 $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 3. f_{MCK} : Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)

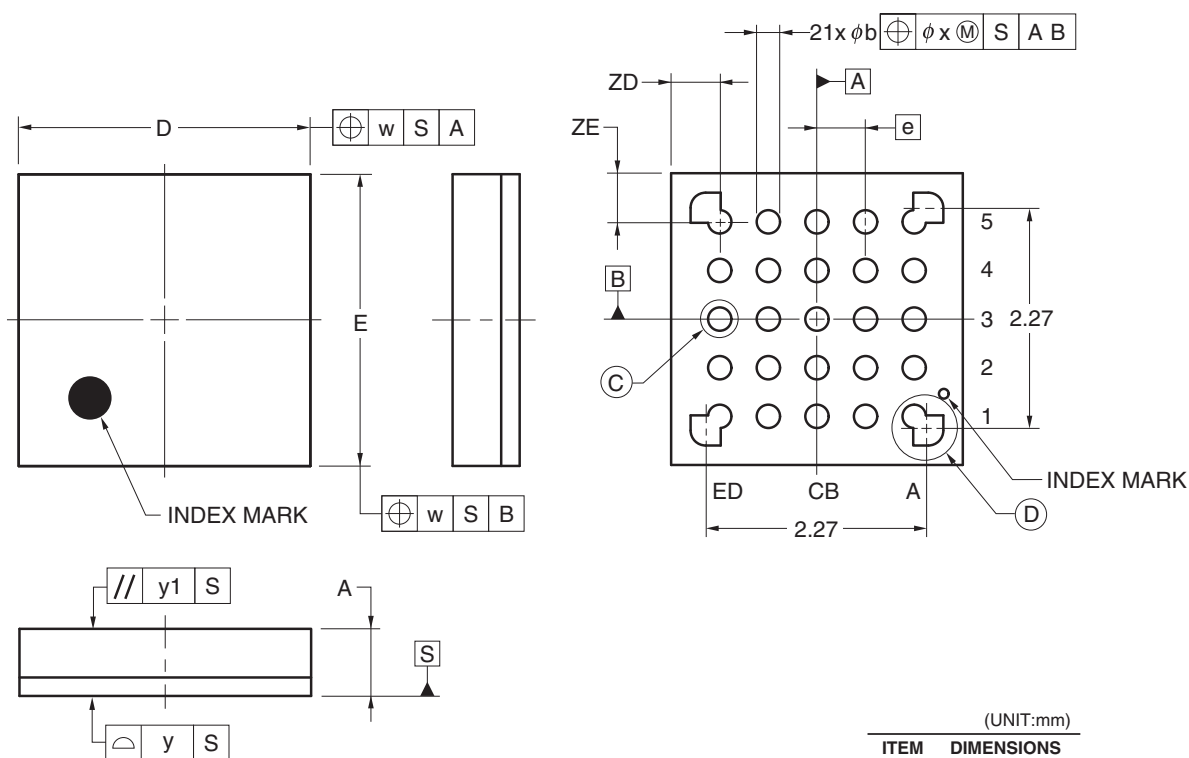


- Remarks**
1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 00, 01, 02, 10, 12, 13), n: Channel number (n = 0, 2), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

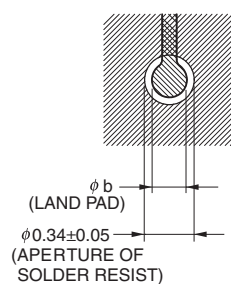
4.3 25-pin Products

R5F1008AALA, R5F1008CALA, R5F1008DALA, R5F1008EALA
 R5F1018AALA, R5F1018CALA, R5F1018DALA, R5F1018EALA
 R5F1008AGLA, R5F1008CGLA, R5F1008DGLA, R5F1008EGLA

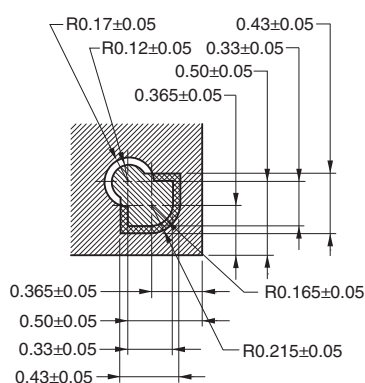
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA25-3x3-0.50	PWLG0025KA-A	P25FC-50-2N2-2	0.01



DETAIL OF © PART



DETAIL OF © PART

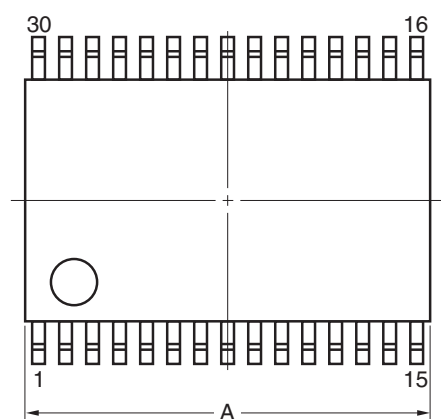


©2012 Renesas Electronics Corporation. All rights reserved.

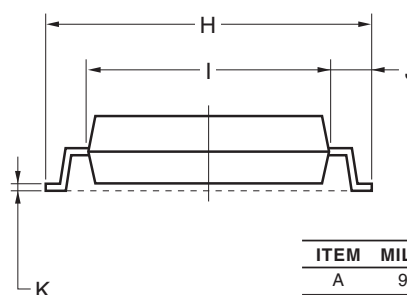
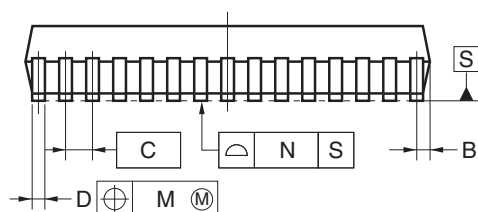
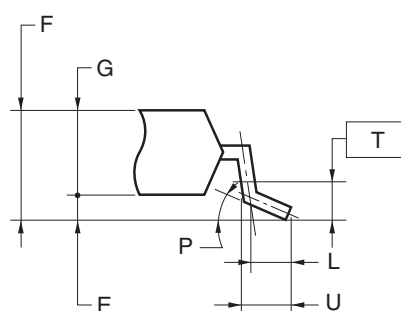
4.4 30-pin Products

R5F100AAASP, R5F100ACASP, R5F100ADASP, R5F100AEASP, R5F100AFASP, R5F100AGASP
 R5F101AAASP, R5F101ACASP, R5F101ADASP, R5F101AEASP, R5F101AFASP, R5F101AGASP
 R5F100AADSP, R5F100ACDSP, R5F100ADDSP, R5F100AEDSP, R5F100AFDSP, R5F100AGDSP
 R5F101AADSP, R5F101ACDSP, R5F101ADDSP, R5F101AEDSP, R5F101AFDSP, R5F101AGDSP
 R5F100AAGSP, R5F100ACGSP, R5F100ADGSP, R5F100AEGSP, R5F100AFGSP, R5F100AGGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18



detail of lead end

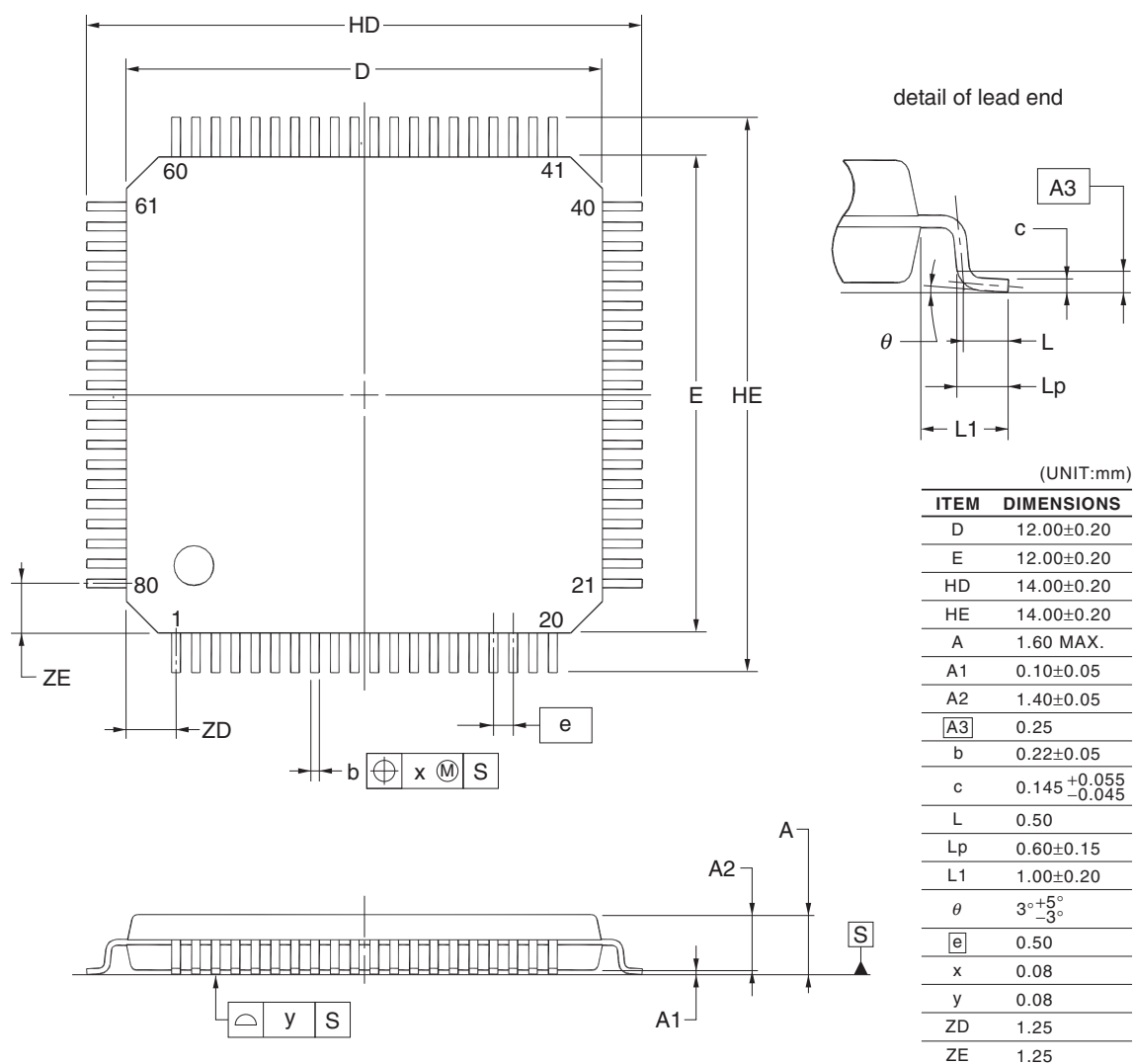
**NOTE**

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	9.85±0.15
B	0.45 MAX.
C	0.65 (T.P.)
D	0.24 ^{+0.08} _{-0.07}
E	0.1±0.05
F	1.3±0.1
G	1.2
H	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
M	0.13
N	0.10
P	3° ^{+5°} _{-3°}
T	0.25
U	0.6±0.15

R5F100MFAFB, R5F100MGAFB, R5F100MHAFB, R5F100MJAFB, R5F100MKAFB, R5F100MLAFB
 R5F101MFAFB, R5F101MGAFB, R5F101MHAFB, R5F101MJAFB, R5F101MKAFB, R5F101MLAFB
 R5F100MFDDB, R5F100MGDFB, R5F100MHDFB, R5F100MJDFB, R5F100MKDFB, R5F100MLDFB
 R5F101MFDDB, R5F101MGDFB, R5F101MHDFB, R5F101MJDFB, R5F101MKDFB, R5F101MLDFB
 R5F100MFGFB, R5F100MGGB, R5F100MHGFB, R5F100MJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP80-12x12-0.50	PLQP0080KE-A	P80GK-50-8EU-2	0.53

**NOTE**

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

©2012 Renesas Electronics Corporation. All rights reserved.

Notice

1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation of these circuits, software, and information in the design of your equipment. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from the use of these circuits, software, or information.
 2. Renesas Electronics has used reasonable care in preparing the information included in this document, but Renesas Electronics does not warrant that such information is error free. Renesas Electronics assumes no liability whatsoever for any damages incurred by you resulting from errors in or omissions from the information included herein.
 3. Renesas Electronics does not assume any liability for infringement of patents, copyrights, or other intellectual property rights of third parties by or arising from the use of Renesas Electronics products or technical information described in this document. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
 4. You should not alter, modify, copy, or otherwise misappropriate any Renesas Electronics product, whether in whole or in part. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from such alteration, modification, copy or otherwise misappropriation of Renesas Electronics product.
 5. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The recommended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below.
"Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; and industrial robots etc.
"High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control systems; anti-disaster systems; anti-crime systems; and safety equipment etc.
Renesas Electronics products are neither intended nor authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems, surgical implantations etc.), or may cause serious property damages (nuclear reactor control systems, military equipment etc.). You must check the quality grade of each Renesas Electronics product before using it in a particular application. You may not use any Renesas Electronics product for any application for which it is not intended. Renesas Electronics shall not be in any way liable for any damages or losses incurred by you or third parties arising from the use of any Renesas Electronics product for which the product is not intended by Renesas Electronics.
 6. You should use the Renesas Electronics products described in this document within the range specified by Renesas Electronics, especially with respect to the maximum rating, operating supply voltage range, movement power voltage range, heat radiation characteristics, installation and other product characteristics. Renesas Electronics shall have no liability for malfunctions or damages arising out of the use of Renesas Electronics products beyond such specified ranges.
 7. Although Renesas Electronics endeavors to improve the quality and reliability of its products, semiconductor products have specific characteristics such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Further, Renesas Electronics products are not subject to radiation resistance design. Please be sure to implement safety measures to guard them against the possibility of physical injury, and injury or damage caused by fire in the event of the failure of a Renesas Electronics product, such as safety design for hardware and software including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult, please evaluate the safety of the final products or systems manufactured by you.
 8. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. Please use Renesas Electronics products in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. Renesas Electronics assumes no liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
 9. Renesas Electronics products and technology may not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You should not use Renesas Electronics products or technology described in this document for any purpose relating to military applications or use by the military, including but not limited to the development of weapons of mass destruction. When exporting the Renesas Electronics products or technology described in this document, you should comply with the applicable export control laws and regulations and follow the procedures required by such laws and regulations.
 10. It is the responsibility of the buyer or distributor of Renesas Electronics products, who distributes, disposes of, or otherwise places the product with a third party, to notify such third party in advance of the contents and conditions set forth in this document, Renesas Electronics assumes no responsibility for any losses incurred by you or third parties as a result of unauthorized use of Renesas Electronics products.
 11. This document may not be reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics.
 12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products, or if you have any other inquiries.
- (Note 1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its majority-owned subsidiaries.
- (Note 2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.



SALES OFFICES

Renesas Electronics Corporation

<http://www.renesas.com>

Refer to "http://www.renesas.com/" for the latest and detailed information.

California Eastern Laboratories, Inc.

4590 Patrick Henry Drive, Santa Clara, California 95054-1817, U.S.A.
Tel: +1-408-919-2500, Fax: +1-408-988-0279

Renesas Electronics Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH

Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.

Room 1709, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100191, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.

Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, P. R. China 200333
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited

Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2265-6688, Fax: +852 2886-9022

Renesas Electronics Taiwan Co., Ltd.

13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.

80 Bendemeer Road, Unit #06-02, Hyflux Innovation Centre, Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.

Unit 1207, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics India Pvt. Ltd.

No.777C, 100 Feet Road, HAL II Stage, Indiranagar, Bangalore, India
Tel: +91-80-67208700, Fax: +91-80-67208777

Renesas Electronics Korea Co., Ltd.

12F., 234 Teheran-ro, Gangnam-Gu, Seoul, 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141